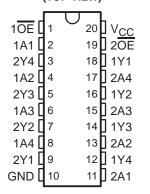
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- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce)
 <0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 >2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} and Power-Up 3-State Support Hot Insertion
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- Package Options Include Shrink Small-Outline (DB), Plastic Thin Very Small-Outline (DGV), Small-Outline (DW), and Thin Shrink Small-Outline (PW) Packages

DB, DGV, DW, OR PW PACKAGE (TOP VIEW)



description

This octal buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCZ240A is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

This device is organized as two 4-bit buffers/drivers with separate output-enable (\overline{OE}) inputs. When \overline{OE} is low, the device passes data from the A inputs to the Y outputs. When \overline{OE} is high, the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

The SN74LVCZ240A is characterized for operation from -40°C to 85°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

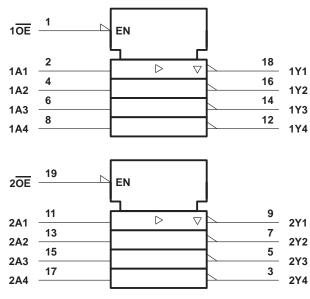
EPIC is a trademark of Texas Instruments Incorporated.



FUNCTION TABLE (each buffer)

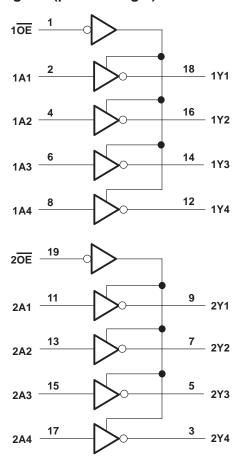
INP	JTS	OUTPUT		
OE	Α	Υ		
L	Н	L		
L	L	Н		
Н	Χ	Z		

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Voltage range applied to any output in the high-impedance or power-off state, V _O (see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	\dots -0.5 V to V _{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	
Continuous current through V _{CC} or GND	
Package thermal impedance, θ_{JA} (see Note 3): DB package	
DGV package	
DW package	97°C/W
PW package	
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

				MAX	UNIT	
Vcc	Supply voltage			3.6	V	
VIH	High-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		V	
V _{IL}	Low-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	V	
VI	Input voltage		0	5.5	V	
\/o	Output veltage		0	VCC	V	
Vo	Output voltage	3-state	0	5.5	V	
la	High-level output current			-12	mA	
ЮН	nigri-level output current	V _{CC} = 3 V		-24	IIIA	
la.	Low lovel output ourrent	V _{CC} = 2.7 V		12	mA	
lOL	Low-level output current	V _{CC} = 3 V	24		IIIA	
Δt/Δν	Input transition rise or fall rate			6	ns/V	
Δt/ΔVCC	Power-up ramp rate			150	μs/V	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST C	ONDITIONS	vcc	MIN	TYP†	MAX	UNIT
	I _{OH} = -100 μA		2.7 V to 3.6 V	V _{CC} -0.2			V
\/a++	I _{OH} = -12 mA		2.7 V	2.2			
VOH			3 V	2.4			
	I _{OH} = -24 mA		3 V	2.2			.
	I _{OL} = 100 μA		2.7 V to 3.6 V			0.2	
VOL	I _{OL} = 12 mA		2.7 V			0.4	V
	I _{OL} = 24 mA		3 V			0.55	
lį	$V_{I} = 0 \text{ to } 5.5 \text{ V}$		3.6 V			±5	μΑ
l _{off}	V_I or $V_O = 5.5 V$		0			±5	μΑ
I _{OZ}	$V_0 = 0 \text{ to } 5.5 \text{ V}$		3.6 V			±5	μΑ
lozpu	$V_0 = 0.5 \text{ to } 2.5 \text{ V},$	OE = don't care	0 to 1.5 V			±5	μΑ
IOZPD	$V_O = 0.5 \text{ to } 2.5 \text{ V},$	OE = don't care	1.5 V to 0			±5	μΑ
laa	$V_I = V_{CC}$ or GND	IO = 0	3.6 V			100	
Icc	$3.6 \text{ V} \le \text{V}_{\text{I}} \le 5.5 \text{ V}^{\ddagger}$					100	μΑ
ΔlCC	One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	2.7 V to 3.6 V			100	μΑ
Ci	$V_I = V_{CC}$ or GND		3.3 V		3.5		pF
Co	$V_O = V_{CC}$ or GND		3.3 V		5.5		pF

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	
t _{pd}	A or B	B or A		7.5	1.3	6.5	ns
t _{en}	ŌĒ	A or B		9	1.1	8	ns
t _{dis}	ŌĒ	A or B		8	1.4	7	ns

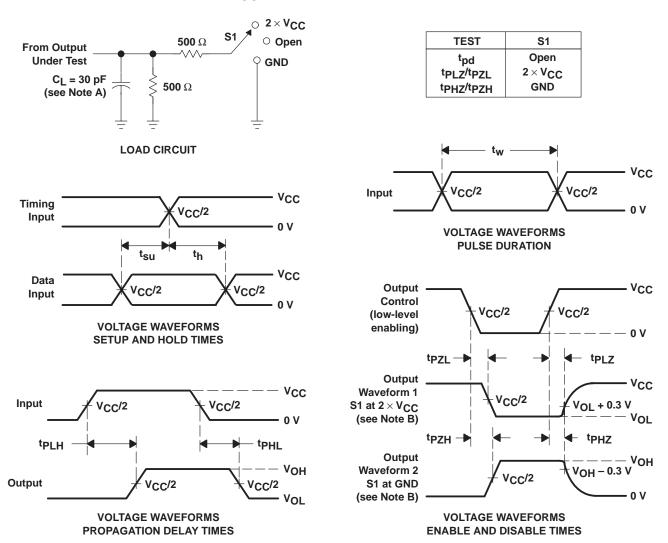
operating characteristics, $T_A = 25^{\circ}C$

PARAMETER			TEST CONDITIONS	V _{CC} = 3.3 V	UNIT	
Const		Outputs enabled	f 40 MH I=	37	ρF	
Cpd	Power dissipation capacitance per buffer/driver	Outputs disabled	f = 10 MHz	3	pr	



[‡] This applies in the disabled state only.

PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2$ ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpl 7 and tpH7 are the same as tdis.
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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